

CD74HCU04-Q1 車載認定済みヘキサ・アンバッファ・インバータ

1 特長

- 車載アプリケーション用に AEC-Q100 認定済み
 - デバイス温度グレード 1: -40°C ~ +125°C、T_A
- 車載アプリケーション認定済み
- バッファなしロジック
- 正負入力クランプ・ダイオード
- 広い動作電圧範囲：2V ~ 6V
- LSTTL ロジック IC に比べて消費電力を大幅削減

2 アプリケーション

- RC 発振回路
- 水晶発振回路

3 概要

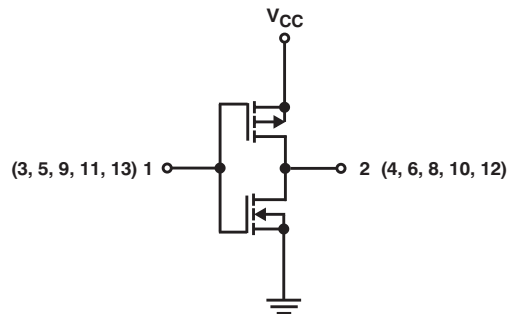
CD74HCU04-Q1 には、6 つの独立した高速 CMOS アンバッファ・インバータが内蔵されています。各インバータはブール関数 $Y = \bar{A}$ を正論理で実行します。

製品情報⁽¹⁾

型番	パッケージ	本体サイズ(公称)
CD74HCU04QPWRQ1	TSSOP (14)	5.00mm × 4.40mm

(1) 提供されているすべてのパッケージについては、データシートの末尾にある注文情報を参照してください。

CD74HCU04-Q1 の機能ピン配置



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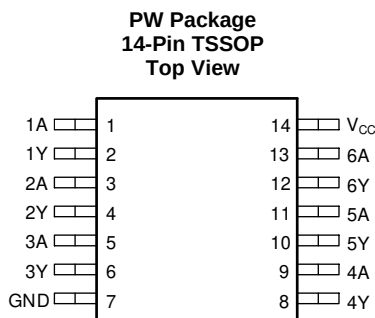
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4 改訂履歴

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Revision (June 2010) から Revision A に変更	Page
• 新しいデータシート規格に更新	1
• Thermal impedance $R_{\theta JA}$ updated from 112.6 to 121.1 °C/W	4

5 Pin Configuration and Functions



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
1A	1	Input	Channel 1, Input A
1Y	2	Output	Channel 1, Output Y
2A	3	Input	Channel 2, Input A
2Y	4	Output	Channel 2, Output Y
3A	5	Input	Channel 3, Input A
3Y	6	Output	Channel 3, Output Y
GND	7	—	Ground
4Y	8	Output	Channel 4, Output Y
4A	9	Input	Channel 4, Input A
5Y	10	Output	Channel 5, Output Y
5A	11	Input	Channel 5, Input A
6Y	12	Output	Channel 6, Output Y
6A	13	Input	Channel 6, Input A
V _{CC}	14	—	Positive Supply

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage		–0.5	7	V
I _{IK}	Input clamp current ⁽²⁾	V _I < 0 or V _I > V _{CC}		±20	mA
I _{OK}	Output clamp current ⁽²⁾	V _O < 0 or V _O > V _{CC}		±20	mA
I _O	Continuous output current	V _O = 0 to V _{CC}		±25	mA
	Continuous current through V _{CC} or GND			±50	mA
T _J	Junction temperature ⁽³⁾			150	°C
T _{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

(3) Guaranteed by design.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 ⁽¹⁾ HBM ESD Classification Level 2	±2000	V
		Charged device model (CDM), per AEC Q100-011 CDM ESD Classification Level C6	±1000	

(1) AEC Q100-002 indicate that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage	2		6	V
V_I	Input voltage	0		V_{CC}	V
V_O	Output voltage	0		V_{CC}	V
T_A	Operating free-air temperature	–40		125	°C

6.4 Thermal Information

THERMAL METRIC		CD74HCU04-Q1	UNIT
		PW (TSSOP)	
		14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	121.1	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	50.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	64.2	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	6.1	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	63.6	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	°C/W

6.5 Electrical Characteristics

over operating free-air temperature range; typical values measured at $T_A = 25^\circ\text{C}$ (unless otherwise noted).

PARAMETER		TEST CONDITIONS		V _{CC}	Operating free-air temperature (T _A)						UNIT	
					25°C			-40°C to 125°C				
					MIN	TYP	MAX	MIN	TYP	MAX		
V _{IH}	High level input voltage			2 V	1.7			1.7			V	
				4.5 V	3.6			3.6				
				6 V	4.8			4.8				
V _{IL}	Low level input voltage			2 V				0.3			V	
				4.5 V				0.8				
				6 V				1.1				
V _{OH}	High-level output voltage	V _I = V _{IH} or V _{IL}	I _{OH} = -20 µA	2 V	1.8			1.8			V	
				4.5 V	4.4			4.4				
				6 V	5.5			5.5				
			I _{OH} = -4 mA	4.5 V	3.98			3.7				
			I _{OH} = -5.2 mA	6 V	5.48			5.2				
V _{OL}	Low-level output voltage	V _I = V _{IH} or V _{IL}	I _{OL} = 20 µA	2 V				0.2			V	
				4.5 V				0.5				
				6 V				0.5				
			I _{OL} = 4 mA	4.5 V	0.26			0.4				
			I _{OL} = 5.2 mA	6 V	0.26			0.4				
I _I	Input leakage current	V _I = V _{CC} or 0		6 V				±0.1			±1	µA
I _{CC}	Supply current	V _I = V _{CC} or 0	I _O = 0	6 V				2			40	µA
C _i	Input capacitance			2 V to 6 V	7							pF

6.6 Switching Characteristics

over operating free-air temperature range (unless otherwise noted), $C_L = 50\ \text{pF}$

PARAMETER		FROM	TO	V _{CC}	Operating free-air temperature (T _A)						UNIT
					25°C			−40°C to 125°C			
					MIN	TYP	MAX	MIN	TYP	MAX	
t _{pd}	Propagation delay	A	Y	2 V	70			105			ns
				4.5 V	14			21			
				6 V	12			18			
t _t	Transition-time		Y	2 V	75			110			ns
				4.5 V	15			22			
				6 V	13			19			

6.7 Operating Characteristics

over operating free-air temperature range; typical values measured at $T_A = 25^\circ\text{C}$ (unless otherwise noted).

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
C_{pd}	Power dissipation capacitance per gate	$V_{CC} = 5\ \text{V}$, No load		14		pF

6.8 Typical Characteristics

$T_A = 25^\circ\text{C}$

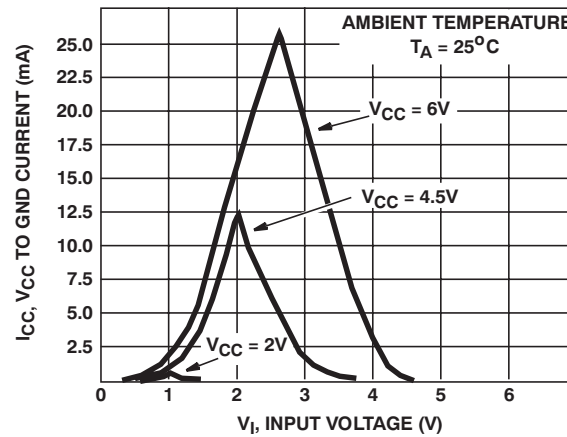


FIG 1. Typical Inverter Supply Current as a Function of Input Voltage

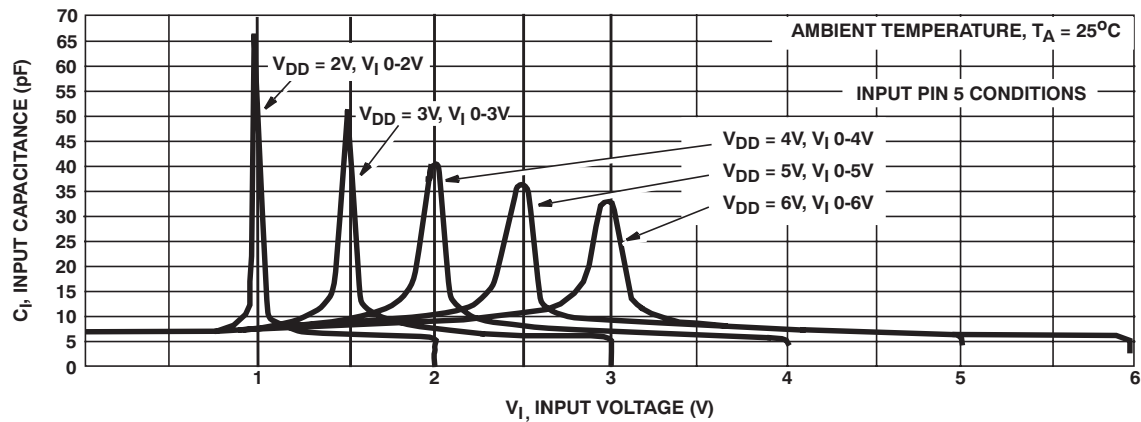
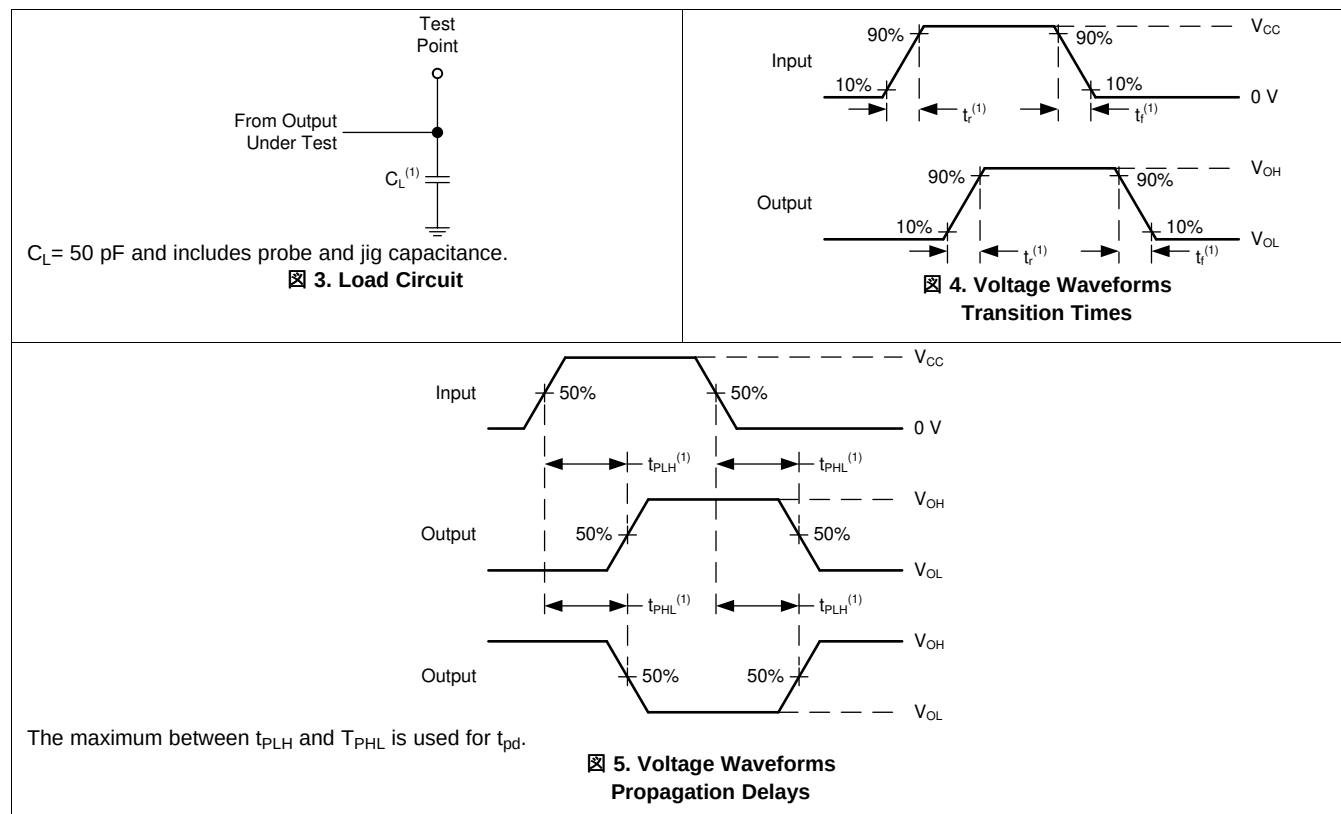


FIG 2. Input Capacitance as a Function of Input Voltage

7 Parameter Measurement Information

- Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: $PRR \leq 1 \text{ MHz}$, $Z_O = 50 \Omega$, $t_t < 6 \text{ ns}$.
- The outputs are measured one at a time, with one input transition per measurement.

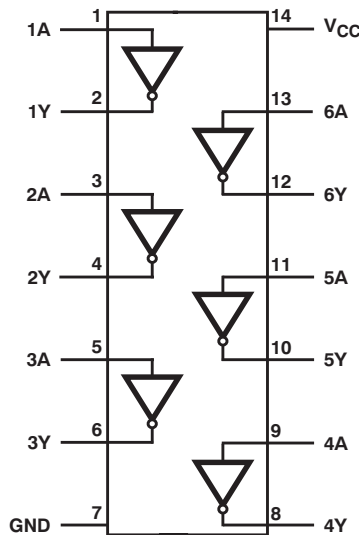


8 Detailed Description

8.1 Overview

The CD74HCU04-Q1 device contains six independent high-speed CMOS unbuffered inverters.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Unbuffered CMOS Logic

Unlike most CMOS logic devices, this device does not include input or output buffers. The input, logic function, and output are all completed by the same set of complementary MOSFETs, as shown in [Figure 6](#).

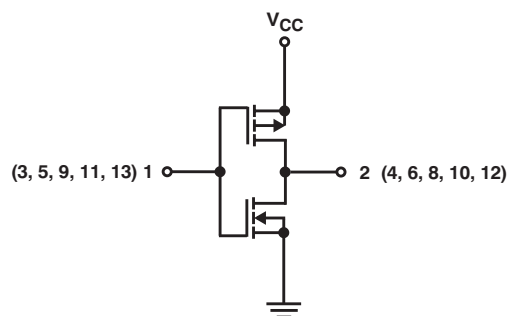


Figure 6. Logic schematic diagram

Each channel of the CD74HCU04-Q1 can drive a load with a total capacitance less than or equal to 50 pF connected to a high-impedance CMOS input while still meeting all of the datasheet specifications. Larger capacitive loads can be applied, however it is not recommended to exceed 70 pF. If larger capacitive loads are required, it is recommended to add a series resistor between the output and the capacitor to limit output current to the values given in the [Absolute Maximum Ratings](#).

Feature Description (continued)

8.3.2 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in [Figure 7](#).

注意

Voltages beyond the values specified in the [Absolute Maximum Ratings](#) table can cause damage to the device. The recommended input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

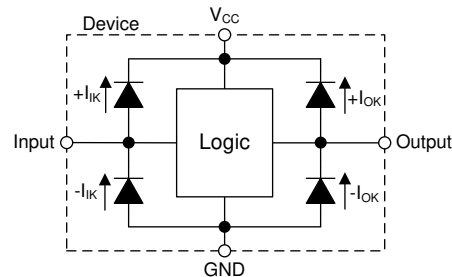


図 7. Electrical Placement of Clamping Diodes for Each Input and Output

8.4 Device Functional Modes

表 1. Function Table

INPUT	OUTPUT
A	Y
L	H
H	L

9 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

In this application, three channels of the CD74HCU04-Q1 are used to create an oscillator circuit as shown in [Figure 8](#). The additional three channels can be used for a second oscillator circuit, used individually for other applications, or the inputs can be grounded and the channels left unused.

The CD74HCU04-Q1 is used in place of an operational amplifier in an oscillator application. Similar to a conventional inverting amplifier design, this oscillator application depends on factors such as open-loop gain, power consumption, and duty-cycle variation with temperature. Unbuffered inverters have a single inverting stage with an AC signal gain in the range of 10 to 20 dB. Buffered inverters, by definition, have more than one stage of inversion and thus much higher gains, typically in the range of 60 to 70 dB. Due to the lower gain, unbuffered inverters help create a more stable oscillator which is less sensitive to parameter changes. The stability of this type of oscillator is sufficient for the majority of applications with frequencies in the range of 100 Hz to 100 kHz.

Frequency accuracy is affected by shifts in temperature, manufacturing process, supply voltage, and values of the external timing components. For applications that require an extremely accurate clock, it is recommended to use a crystal oscillator circuit or a dedicated oscillator IC instead.

9.2 Typical Application

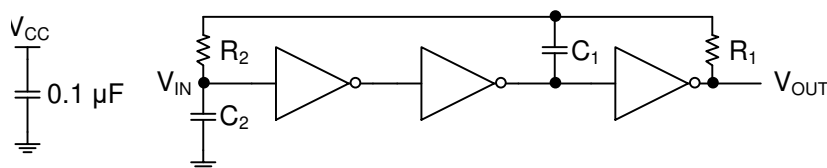


图 8. Typical application schematic

9.2.1 Design Requirements

- This design utilizes a 5-V supply voltage, resulting in a 5-V output waveform.
- Low variance components should be used for the timing components (R_1 , R_2 , C_1 , C_2) as changes in these component values will cause changes in output frequency.
- For this application R_1 must have a much lower value than R_2 ($R_1 \ll R_2$).
- Short trace lengths will improve oscillator stability by reducing parasitics.

9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the [Recommended Operating Conditions](#). The supply voltage sets the device's electrical characteristics as described in the [Electrical Characteristics](#). Changes to the supply will change the characteristics of the inverter, which will also change the oscillation frequency slightly.

Because the oscillator circuit biases two of the three stages of the device at approximately $V_{CC}/2$, both MOSFETs in the channels will be turned on and the supply current (I_{CC}) through the device will be much larger than that shown for operation as a CMOS logic device in the I_{CC} specification in the [Electrical Characteristics](#). This value will typically be between 10 and 30 mA per oscillator circuit.

The supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the CD74HCU04-Q1 plus the maximum supply current, I_{CC} , listed in the [Electrical Characteristics](#). The logic device can only source or sink as much current as it is provided at the supply and ground pins, respectively. Be sure not to exceed the maximum total current through GND or V_{CC} listed in the [Absolute Maximum Ratings](#).

Typical Application (continued)

Total power consumption can be calculated using the information provided in [CMOS Power Consumption and \$C_{pd}\$ Calculation](#).

Thermal increase can be calculated using the information provided in [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices](#).

注意

The maximum junction temperature, $T_J(\text{max})$ listed in the [Absolute Maximum Ratings](#), is an *additional limitation* to prevent damage to the device. Do not violate any values listed in the [Absolute Maximum Ratings](#). These limits are provided to prevent damage to the device.

9.2.1.2 Input Considerations

Although the oscillator circuit described in [Application Information](#) does not exactly have an input, the CD74HCU04-Q1 device does have inputs. Be sure to connect all inputs either to a valid logic circuit or as part of the oscillator circuit provided. Attaching oscilloscope probes to nodes of an oscillator circuit can cause shifts in the operating frequency, especially if the timing capacitor values are very small (less than 100 pF).

Unused inputs must be terminated to either V_{CC} or ground. These inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the CD74HCU04-Q1, as specified in the [Electrical Characteristics](#), and the desired input transition rate. A 10-k Ω resistor value is often used due to these factors.

Refer to the [Feature Description](#) for additional information regarding the inputs for this device.

9.2.1.3 Output Considerations

The output of the oscillator is a square wave at the supply voltage. This signal can be passed through an additional buffer or inverter stage to add additional drive strength without affecting the operation of the oscillator circuit.

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the [Electrical Characteristics](#). Similarly, the ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the [Electrical Characteristics](#). Unused outputs can be left floating.

Refer to [Feature Description](#) for additional information regarding the outputs for this device.

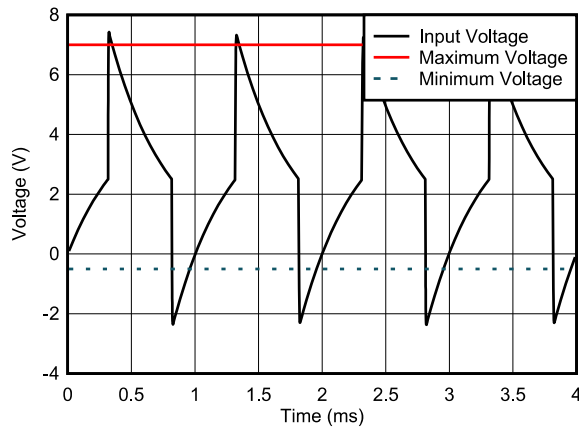
9.2.2 Detailed Design Procedure

1. Decide the frequency of operation required. Adjustments to the calculated values of the components may be required to get the desired frequency.
2. For the purpose of this design, we will not include C_2 and instead use the internal input capacitance of the buffer which is approximately 15 pF. C_2 should be added to the circuit to reduce overshoot and undershoot conditions on the inputs as shown in [Application Curves](#). Increasing the value of C_2 will slightly decrease the available output frequency.
3. To simplify the design, R_2 can be set to a large value. 100 k Ω is a good choice. Decreasing R_2 will slightly increase the available output frequency but will also increase the overshoot and undershoot on the input of the first buffer as shown in [Application Curves](#). The input signal should never exceed the absolute maximum ratings of the device.
4. Use the equation $f = 1/(2.2R_1C_1)$ to calculate the resistor and capacitor values for the desired frequency. Keep in mind the requirement that the value of $R_1 \ll R_2$ for the equation to remain valid.
5. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in [Layout](#).

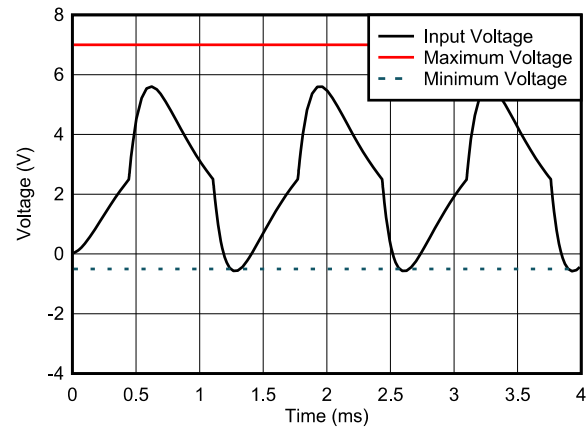
Typical Application (continued)

6. Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit, however it will ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the CD74HCU04-Q1 to the receiving device.
7. Testing this circuit in a simulation tool can be helpful for building confidence in the design, but it is necessary to build a prototype to guarantee proper operation as many factors can impact the stability of this oscillator.
8. Thermal issues are rarely a concern for logic gates, however the power consumption and thermal increase can be calculated using the steps provided in the application report, [CMOS Power Consumption and Cpd Calculation](#)

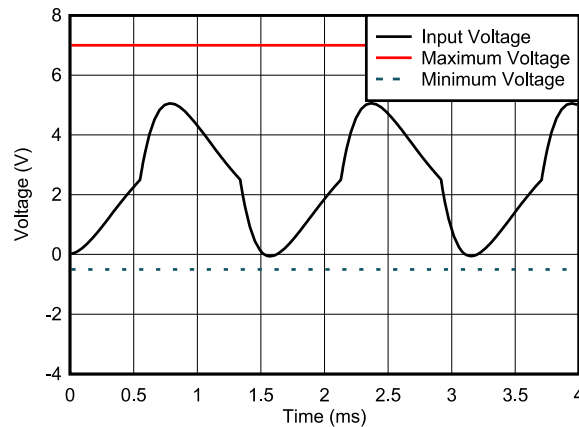
9.2.3 Application Curves



⊠ 9. First stage input waveform with excessive overshoot and undershoot



⊠ 10. First stage input waveform with marginal overshoot and undershoot



⊠ 11. First stage input waveform for optimized circuit

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the [Recommended Operating Conditions](#). Each V_{CC} terminal should have a bypass capacitor to prevent power disturbance. A 0.1- μ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in [Figure 12](#).

11 Layout

11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.

11.2 Layout Example

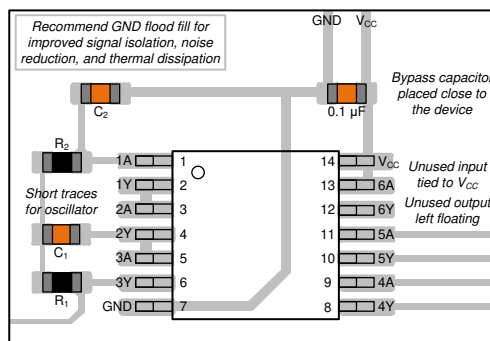


Figure 12. Example layout for the CD74HCU04-Q1

12 デバイスおよびドキュメントのサポート

12.1 ドキュメントのサポート

12.1.1 関連資料

関連資料については、以下を参照してください。

- 『[Use of the CMOS Unbuffered Inverter in Oscillator Circuits](#)』(英語)
- 『[HCMOS Design Considerations](#)』(英語)
- 『[CMOS Power Consumption and Cpd Calculation](#)』(英語)
- 『[Designing With Logic](#)』(英語)

12.2 関連リンク

次の表に、クイック・アクセス・リンクを示します。カテゴリには、技術資料、サポートおよびコミュニティ・リソース、ツールとソフトウェア、およびサンプル注文またはご購入へのクイック・アクセスが含まれます。

12.3 コミュニティ・リソース

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

12.4 商標

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

12.5 静電気放電に関する注意事項



これらのデバイスは、限定的なESD(静電破壊)保護機能を内蔵しています。保存時または取り扱い時は、MOSゲートに対する静電破壊を防止するために、リード線同士をショートさせておくか、デバイスを導電フォームに入れる必要があります。

12.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスについて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CD74HCU04QPWRQ1	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HJU04Q	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

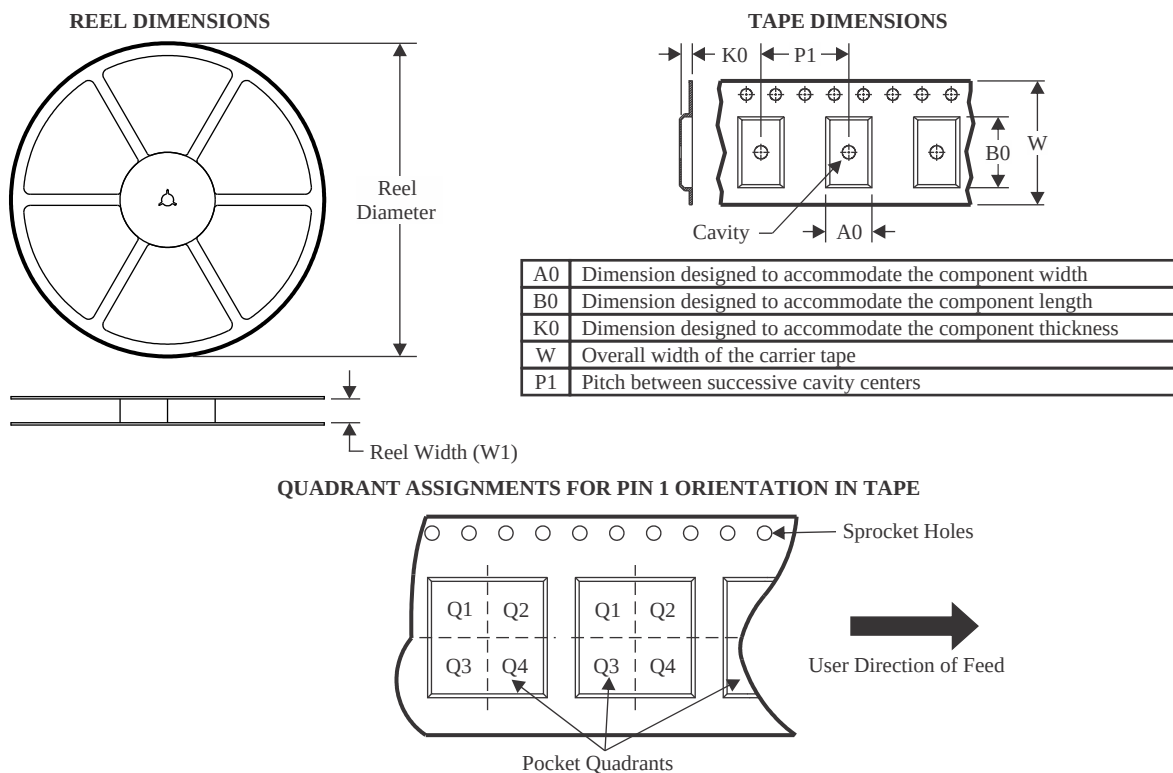
(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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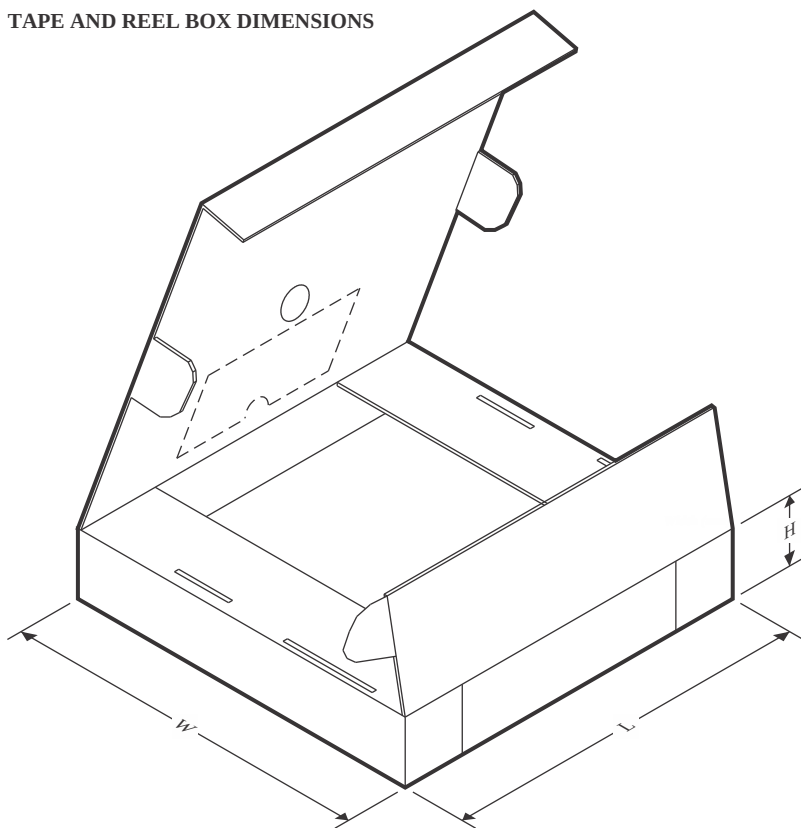
TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CD74HCU04QPWRQ1	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS

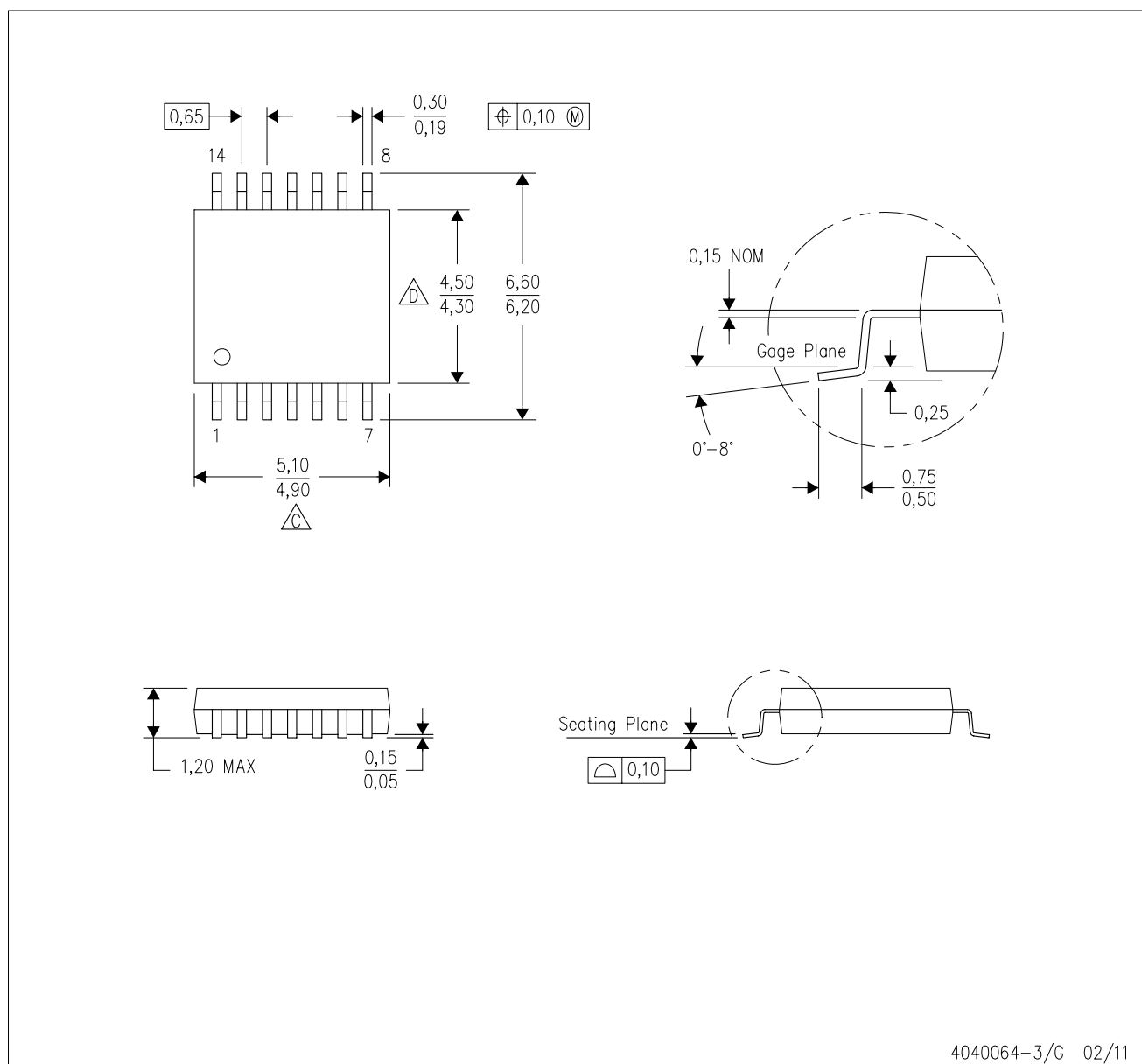


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CD74HCU04QPWRQ1	TSSOP	PW	14	2000	356.0	356.0	35.0

PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE

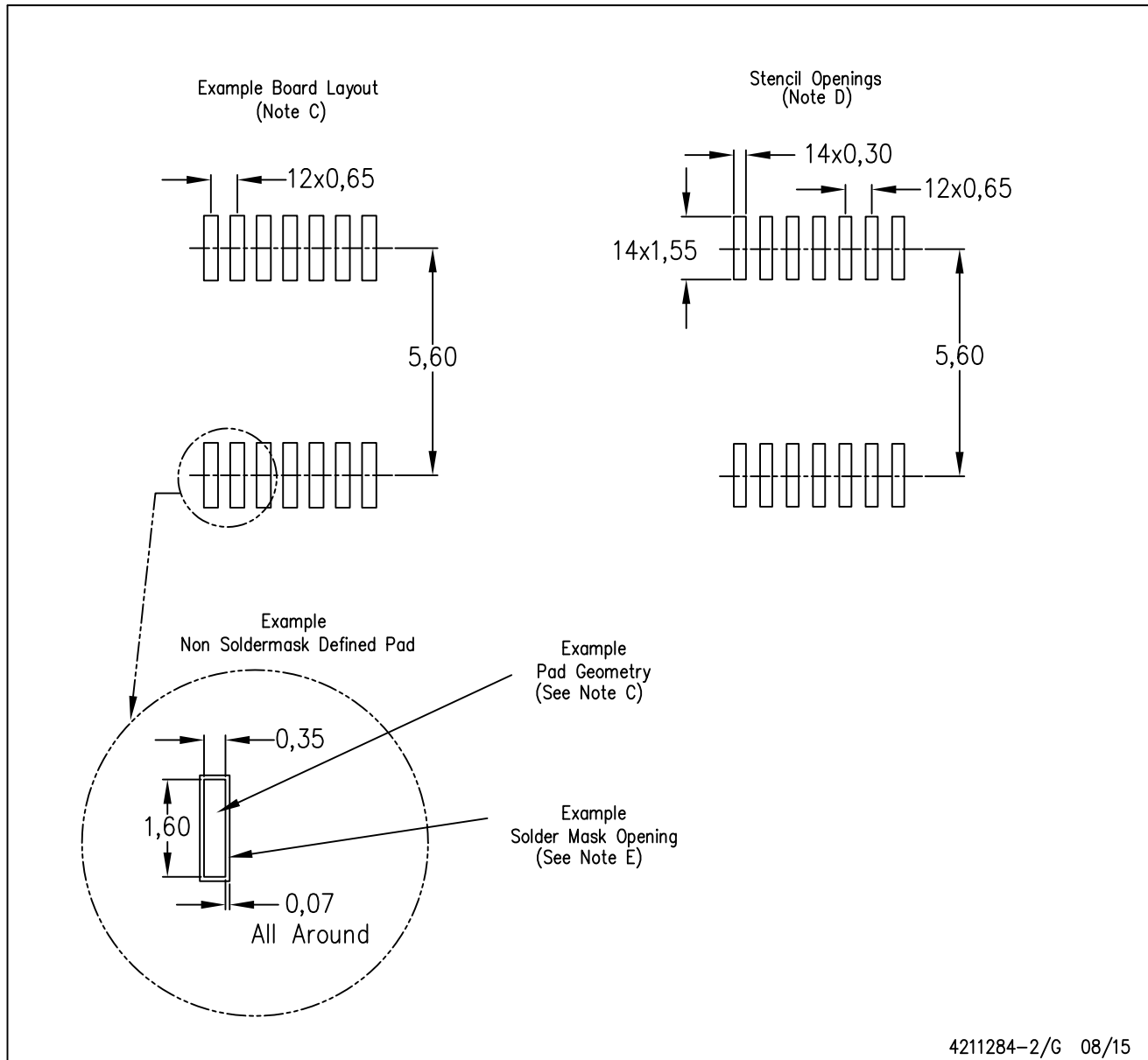


4040064-3/G 02/11

- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - B. This drawing is subject to change without notice.
 - C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
 - D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
 - E. Falls within JEDEC MO-153

PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Publication IPC-7351 is recommended for alternate designs.
 - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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